

# 54ACT899

## 9-Bit Latchable Transceiver with Parity Generator/Checker

### General Description

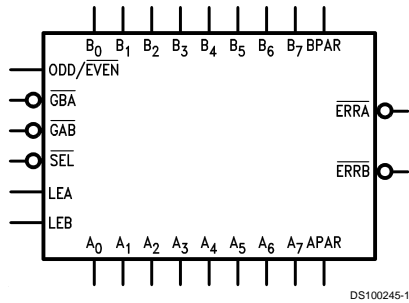
The ACT899 is a 9-bit to 9-bit parity transceiver with transparent latches. The device can operate as a feed-through transceiver or it can generate/check parity from the 8-bit data busses in either direction. The ACT899 features independent latch enables for the A-to-B direction and the B-to-A direction, a select pin for ODD/EVEN parity, and separate error signal output pins for checking parity.

- Independent latch enable for A-to-B and B-to-A directions
- Select pin for ODD/EVEN parity
- $\overline{ERRA}$  and  $\overline{ERRB}$  output pins for parity checking
- Ability to simultaneously generate and check parity
- May be used in system applications in place of the '280
- May be used in system applications in place of the '657 and '373 (no need to change T/R to check parity)
- 4 kV minimum ESD immunity
- Standard Microcircuit Drawing (SMD) 5962-9314101

### Features

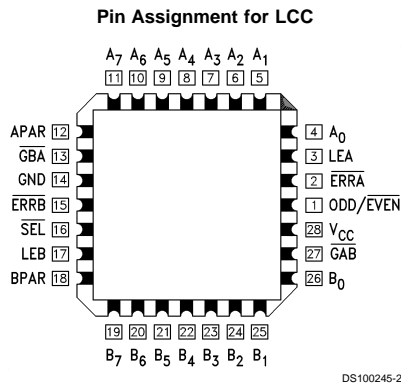
- Latchable transceiver with output sink of 24 mA
- Option to select generate parity and check or "feed-through" data/parity in directions A-to-B or B-to-A

### Logic Symbol



Pin Names	Description
A <sub>0</sub> -A <sub>7</sub>	A Bus Data Inputs/Data Outputs
B <sub>0</sub> -B <sub>7</sub>	B Bus Data Inputs/Data Outputs
APAR, BPAR	A and B Bus Parity Inputs
ODD/EVEN	ODD/EVEN Parity Select, Active LOW for EVEN Parity
$\overline{GAB}$ , $\overline{GBA}$	Output Enables for A or B Bus, Active LOW
SEL	Select Pin for Feed-Through or Generate Mode, LOW for Generate Mode
LEA, LEB	Latch Enables for A and B Latches, HIGH for Transparent Mode
$\overline{ERRA}$ , $\overline{ERRB}$	Error Signals for Checking Generated Parity with Parity In, LOW if Error Occurs

### Connection Diagram



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FACT® is a registered trademark of Fairchild Semiconductor Corporation.

## Functional Description

The ACT899 has three principal modes of operation which are outlined below. These modes apply to both the A-to-B and B-to-A directions.

- Bus A (B) communicates to Bus B (A), parity is generated and passed on to the B (A) Bus as BPAR (APAR). If LEB (LEA) is HIGH and the Mode Select ( $\overline{\text{SEL}}$ ) is LOW, the parity generated from B[0:7] (A[0:7]) can be checked and monitored by ERRB (ERRA).
- Bus A (B) communicates to Bus B (A) in a feed-through mode if  $\overline{\text{SEL}}$  is HIGH. Parity is still generated and checked as  $\overline{\text{ERRA}}$  and  $\overline{\text{ERRB}}$  in the feed-through mode (can be used as an interrupt to signal a data/parity bit error to the CPU).
- Independent Latch Enables (LEA and LEB) allow other permutations of generating/checking (see Function Table below).

## Function Table

Inputs					Operation
$\overline{\text{GAB}}$	$\overline{\text{GBA}}$	$\overline{\text{SEL}}$	LEA	LEB	
H	H	X	X	X	Busses A and B are TRI-STATE®.
H	L	L	L	H	Generates parity from B[0:7] based on $\text{O}/\overline{\text{E}}$ (Note 1). Generated parity $\rightarrow$ APAR. Generated parity checked against BPAR and output as $\overline{\text{ERRB}}$ .
H	L	L	H	H	Generates parity from B[0:7] based on $\text{O}/\overline{\text{E}}$ . Generated parity $\rightarrow$ APAR. Generated parity checked against BPAR and output as $\overline{\text{ERRB}}$ . Generated parity also fed back through the A latch for generate/check as $\overline{\text{ERRA}}$ .
H	L	L	X	L	Generates parity from B latch data based on $\text{O}/\overline{\text{E}}$ . Generated parity $\rightarrow$ APAR. Generated parity checked against latched BPAR and output as $\overline{\text{ERRB}}$ .
H	L	H	X	H	BPAR/B[0:7] $\rightarrow$ APAR/A[0:7] Feed-through mode. Generated parity checked against BPAR and output as $\overline{\text{ERRB}}$ .
H	L	H	H	H	BPAR/B[0:7] $\rightarrow$ APAR/A[0:7] Feed-through mode. Generated parity checked against BPAR and output as $\overline{\text{ERRB}}$ . Generated parity also fed back through the A latch for generate/check as $\overline{\text{ERRA}}$ .
L	H	L	H	L	Generates parity for A[0:7] based on $\text{O}/\overline{\text{E}}$ . Generated parity $\rightarrow$ BPAR. Generated parity checked against APAR and output as $\overline{\text{ERRA}}$ .
L	H	L	H	H	Generates parity from A[0:7] based on $\text{O}/\overline{\text{E}}$ . Generated parity $\rightarrow$ BPAR. Generated parity checked against APAR and output as $\overline{\text{ERRA}}$ . Generated parity also fed back through the B latch for generate/check as $\overline{\text{ERRB}}$ .
L	H	L	L	X	Generates parity from A latch data based on $\text{O}/\overline{\text{E}}$ . Generated parity $\rightarrow$ BPAR. Generated parity checked against latched APAR and output as $\overline{\text{ERRA}}$ .
L	H	H	H	L	APAR/A[0:7] $\rightarrow$ BPAR/B[0:7] Feed-through mode. Generated parity checked against APAR and output as $\overline{\text{ERRA}}$ .
L	H	H	H	H	APAR/A[0:7] $\rightarrow$ BPAR/B[0:7] Feed-through mode. Generated parity checked against APAR and output as $\overline{\text{ERRA}}$ . Generated parity also fed back through the B latch for generate/check as $\overline{\text{ERRB}}$ .

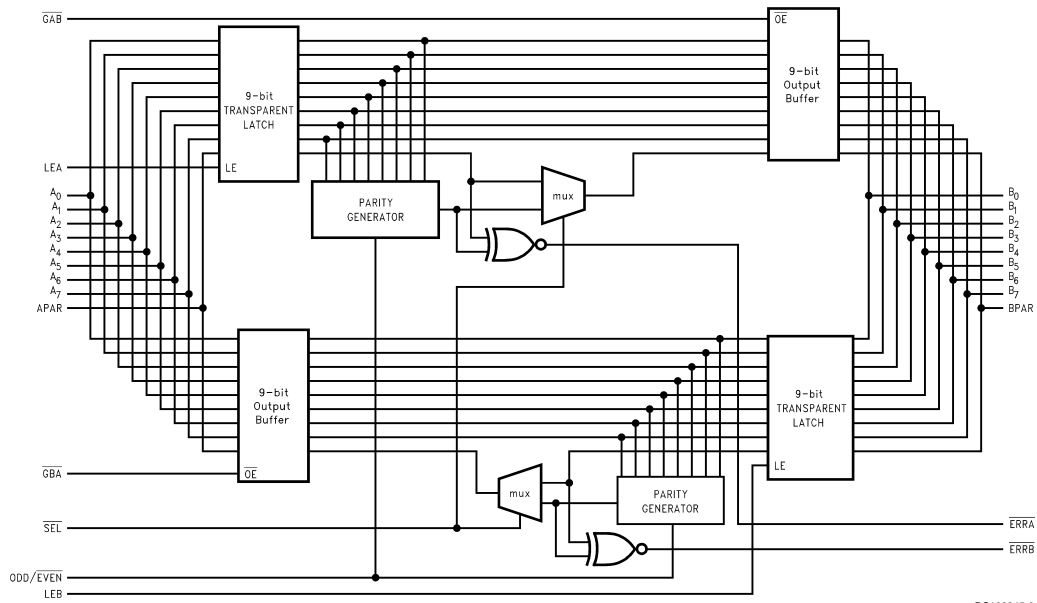
H = HIGH Voltage Level

L = LOW Voltage Level

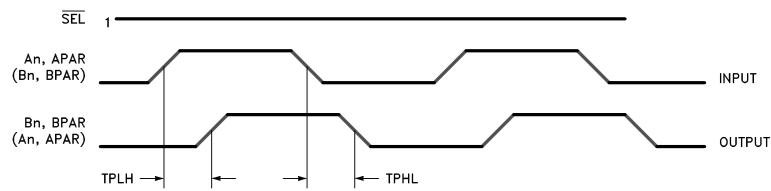
X = Immaterial

**Note 1:**  $\text{O}/\overline{\text{E}}$  = ODD/ $\overline{\text{EVEN}}$

## Functional Block Diagram

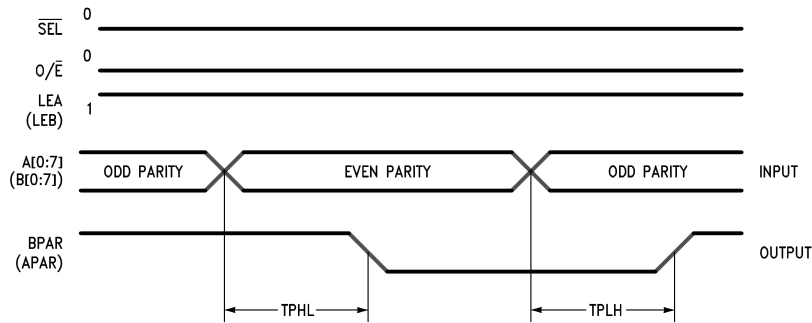


## AC Path



$A_n, APAR \rightarrow B_n, BPAR$   
 $(B_n, BPAR \rightarrow A_n, APAR)$

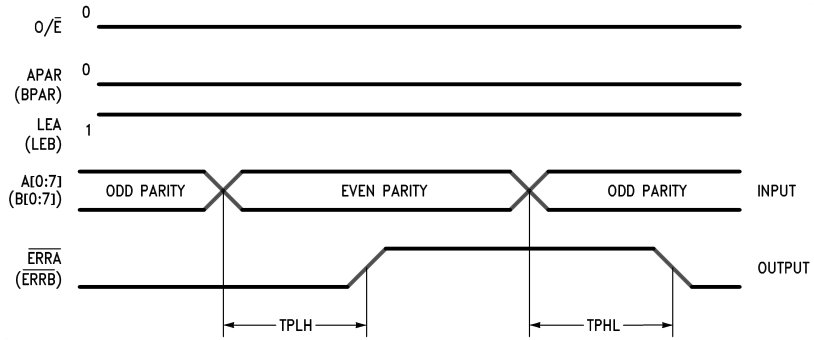
FIGURE 1.



$A_n \rightarrow BPAR$   
 $(B_n \rightarrow APAR)$

FIGURE 2.

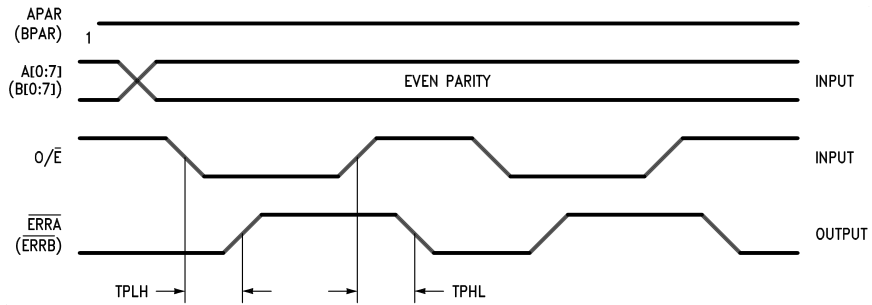
### AC Path (Continued)



$A_n \rightarrow \overline{ERRA}$   
 $(B_n \rightarrow \overline{ERRB})$

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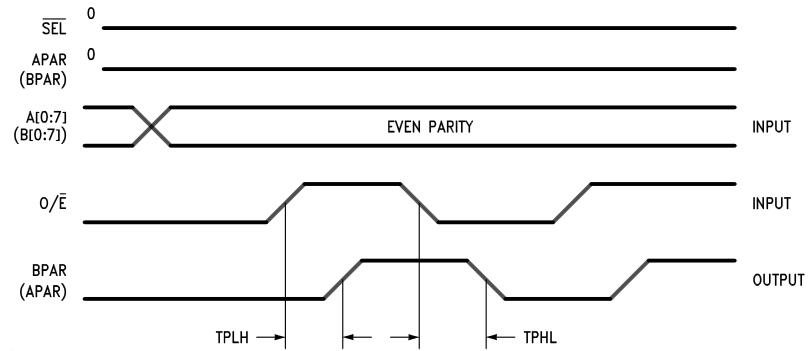
FIGURE 3.



$O/\bar{E} \rightarrow \overline{ERRA}$   
 $O/\bar{E} \rightarrow \overline{ERRB}$

DS100245-7

FIGURE 4.

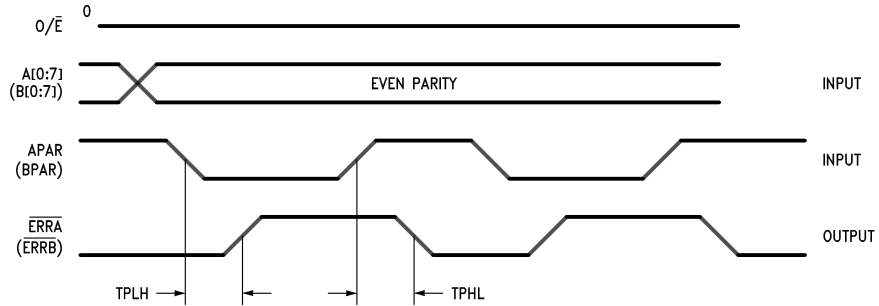


$O/\bar{E} \rightarrow BPAR$   
 $(O/\bar{E} \rightarrow APAR)$

DS100245-8

FIGURE 5.

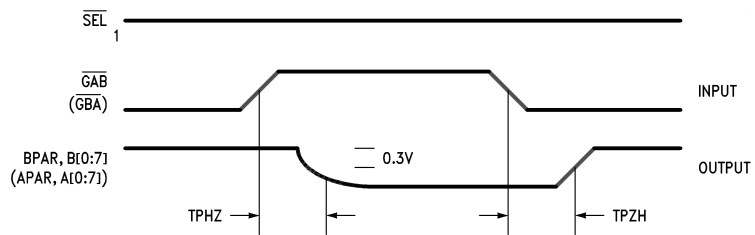
## AC Path (Continued)



DS100245-9

$APAR \rightarrow \overline{ERRA}$   
 $BPAR \rightarrow \overline{ERRB}$

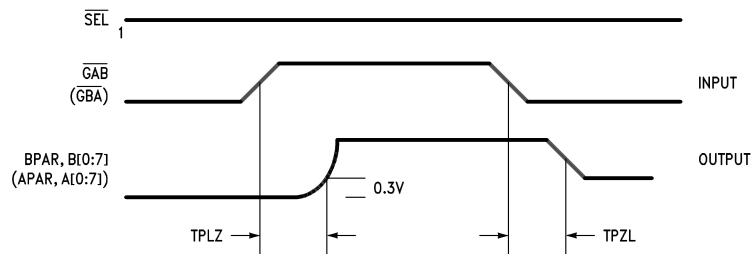
FIGURE 6.



DS100245-10

ZH, HZ

FIGURE 7.

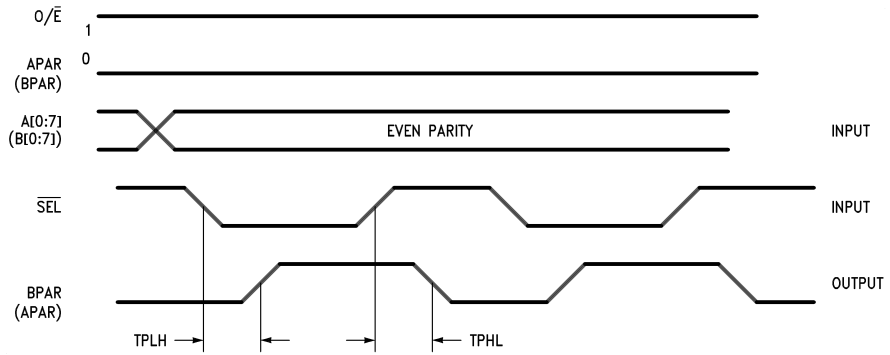


DS100245-11

ZL, LZ

FIGURE 8.

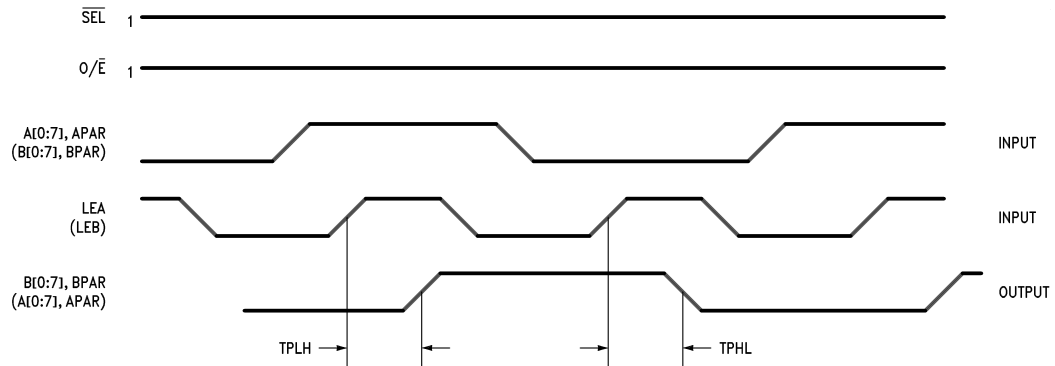
**AC Path** (Continued)



DS100245-12

$\overline{SEL} \rightarrow$  BPAR  
( $\overline{SEL} \rightarrow$  APAR)

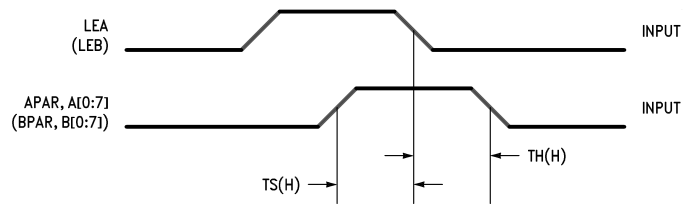
**FIGURE 9.**



DS100245-13

LEA  $\rightarrow$  BPAR, B[0:7]  
(LEB  $\rightarrow$  APAR, A[0:7])

**FIGURE 10.**

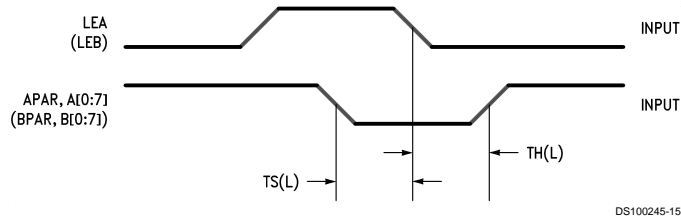


DS100245-14

TS(H), TH(H)  
LEA  $\rightarrow$  APAR, A[0:7]  
(LEB  $\rightarrow$  BPAR, B[0:7])

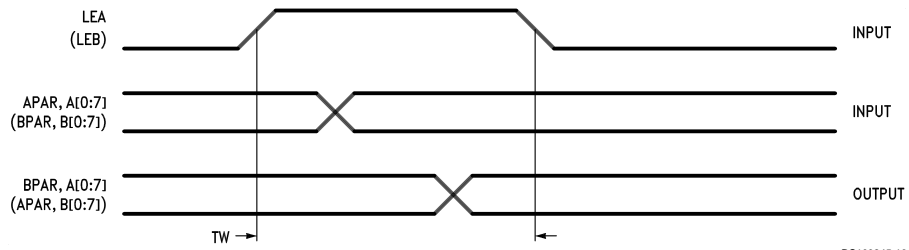
**FIGURE 11.**

**AC Path** (Continued)



TS(L), TH(L)  
 LEA → APAR, A[0:7]  
 (LEB → BPAR, B[0:7])

**FIGURE 12.**



**FIGURE 13.**

### Absolute Maximum Ratings (Note 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	-0.5V to +7.0V
DC Input Diode Current ( $I_{IK}$ )	
$V_I = -0.5V$	-20 mA
$V_I = V_{CC} + 0.5V$	+20 mA
DC Input Voltage ( $V_I$ )	-0.5V to $V_{CC} + 0.5V$
DC Output Diode Current ( $I_{OK}$ )	
$V_O = -0.5V$	-20 mA
$V_O = V_{CC} + 0.5V$	+20 mA
DC Output Voltage ( $V_O$ )	-0.5V to $V_{CC} + 0.5V$
DC Output Source	
or Sink Current ( $I_O$ )	±50 mA
DC $V_{CC}$ or Ground Current	
per Output Pin ( $I_{CC}$ or $I_{GND}$ )	±50 mA
Storage Temperature ( $T_{STG}$ )	-65°C to +150°C

DC Latch-Up Source or

Sink Current	±300 mA
Junction Temperature ( $T_J$ )	
CDIP	175°C

### Recommended Operating Conditions

Supply Voltage ( $V_{CC}$ )	
'ACT	4.5V to 5.5V
Input Voltage ( $V_I$ )	0V to $V_{CC}$
Output Voltage ( $V_O$ )	0V to $V_{CC}$
Operating Temperature ( $T_A$ )	
54ACT	-55°C to +125°C
Minimum Input Edge Rate $\Delta V/\Delta t$	
'ACT Devices	
$V_{IN}$ from 0.8V to 2.0V	
$V_{CC}$ @ 4.5V, 5.5V	125 mV/ns

**Note 2:** Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of FACT® circuits outside databook specifications.

**Note 3:** PLCC packaging is not recommended for applications requiring greater than 2000 temperature cycles from -40°C to +125°C.

### DC Electrical Characteristics for 'ACT Family Devices

Symbol	Parameter	$V_{CC}$ (V)	54ACT	Units	Conditions
			$T_A =$ -55°C to +125°C		
			Guaranteed Limits		
$V_{IH}$	Minimum High Level Input Voltage	4.5	2.0	V	$V_{OUT} = 0.1V$ or $V_{CC} - 0.1V$
		5.5	2.0		
$V_{IL}$	Maximum Low Level Input Voltage	4.5	0.8	V	$V_{OUT} = 0.1V$ or $V_{CC} - 0.1V$
		5.5	0.8		
$V_{OH}$	Minimum High Level Output Voltage	4.5	4.4	V	$I_{OUT} = -50 \mu A$
		5.5	5.4		
		4.5	3.70	V	(Note 4) $V_{IN} = V_{IL}$ or $V_{IH}$ $I_{OH} = -24 mA$ $I_{OH} = -24 mA$
		5.5	4.70		
$V_{OL}$	Maximum Low Level Output Voltage	4.5	0.1	V	$I_{OUT} = 50 \mu A$
		5.5	0.1		
		4.5	0.50	V	(Note 4) $V_{IN} = V_{IL}$ or $V_{IH}$ $I_{OL} = 24 mA$ $I_{OL} = 24 mA$
		5.5	0.50		
$I_{IN}$	Maximum Input Leakage Current	5.5	±1.0	µA	$V_I = V_{CC}, GND$
$I_{OZ}$	Maximum TRI-STATE Leakage Current	5.5	±10.0	µA	$V_I = V_{IL}, V_{IH}$ $V_O = V_{CC}, GND$
$I_{CCT}$	Maximum $I_{CC}$ /Input	5.5	1.6	mA	$V_I = V_{CC} - 2.1V$
$I_{OLD}$	Minimum Dynamic	5.5	50	mA	$V_{OLD} = 1.65V Max$
$I_{OHD}$	Output Current (Note 5)	5.5	-50	mA	$V_{OHD} = 3.85V Min$



## DC Electrical Characteristics for 'ACT Family Devices (Continued)

Symbol	Parameter	V <sub>CC</sub> (V)	54ACT		Units	Conditions
			T <sub>A</sub> = -55°C to +125°C			
			Guaranteed Limits			
I <sub>CC</sub>	Maximum Quiescent Supply Current	5.5	160.0		μA	V <sub>IN</sub> = V <sub>CC</sub> or GND (Note 6)

**Note 4:** Maximum of 9 outputs loaded; thresholds on input associated with output under test.

**Note 5:** Maximum test duration 2.0 ms, one output loaded at a time.

**Note 6:** I<sub>CC</sub> for 54ACT @ 25°C is identical to 74ACT @ 25°C.

## AC Electrical Characteristics

Symbol	Parameter	V <sub>CC</sub> (V) (Note 7)	54ACT		Units	Fig. No.
			T <sub>A</sub> = -55°C to +125°C C <sub>L</sub> = 50 pF			
			Min	Max		
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay A <sub>n</sub> , B <sub>n</sub> to B <sub>n</sub> , A <sub>n</sub>	5.0	1.5	13.5	ns	Figure 1
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay APAR, BPAR to BPAR, APAR	5.0	1.5	11.0	ns	Figure 1
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay A <sub>n</sub> , B <sub>n</sub> to BPAR, APAR	5.0	1.5	16.0	ns	Figure 2
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay A <sub>n</sub> , B <sub>n</sub> to $\overline{ERRA}$ , $\overline{ERRB}$	5.0	1.5	16.0	ns	Figure 3
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay ODD/ $\overline{EVEN}$ to $\overline{ERRA}$ , $\overline{ERRB}$	5.0	1.5	16.0	ns	Figure 4
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay ODD/ $\overline{EVEN}$ to APAR, BPAR	5.0	1.5	14.5	ns	Figure 5
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay APAR, BPAR to $\overline{ERRA}$ , $\overline{ERRB}$	5.0	1.5	11.5	ns	Figure 6
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay $\overline{SEL}$ to APAR, BPAR	5.0	1.5	12.5	ns	Figure 9
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay LEB to A <sub>n</sub> , B <sub>n</sub>	5.0	1.5	13.5	ns	Figures 10, 11
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay LEA to APAR, BPAR	5.0	1.5	16.0	ns	Figures 10, 11
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay LEA, LEB to $\overline{ERRA}$ , $\overline{ERRB}$	5.0	1.5	16.0	ns	Figure 12
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time $\overline{GBA}$ or $\overline{GAB}$ to A <sub>n</sub> , B <sub>n</sub>	5.0	1.5	16.0	ns	Figures 7, 8
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time $\overline{GBA}$ or $\overline{GAB}$ to BPAR or APAR	5.0	1.5	11.0	ns	Figures 7, 8
t <sub>PHZ</sub> t <sub>PHL</sub>	Output Disable Time $\overline{GBA}$ or $\overline{GAB}$ to A <sub>n</sub> , B <sub>n</sub>	5.0	1.5	11.0	ns	Figures 7, 8
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time $\overline{GBA}$ or $\overline{GAB}$ to BPAR, APAR	5.0	1.5	11.0	ns	Figures 7, 8

**Note 7:** Voltage Range 5.0 is 5.0V ± 0.5V.

## AC Operating Requirements

Symbol	Parameter	V <sub>CC</sub> (V) (Note 8)	54ACT	Units	Fig. No.
			T <sub>A</sub> = -55°C to +125°C C <sub>L</sub> = 50 pF		
			Guaranteed Minimum		
t <sub>s</sub>	Setup Time, HIGH or LOW A <sub>n</sub> , B <sub>n</sub> , PAR to LEA, LEB	5.0	3.0	ns	Figures 11, 12
t <sub>h</sub>	Hold Time, HIGH or LOW A <sub>n</sub> , B <sub>n</sub> , PAR to LEA, LEB	5.0	3.0	ns	Figures 11, 12
t <sub>w</sub>	Pulse Width for LEB, LEA	5.0	4.0	ns	Figure 13

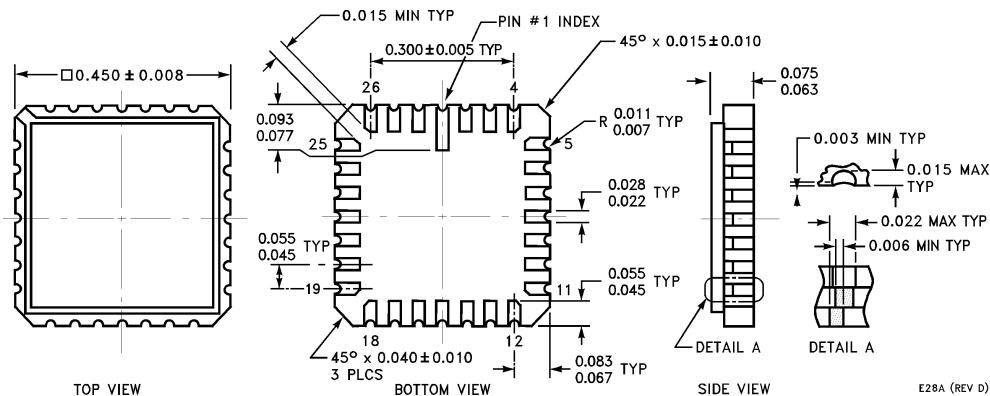
**Note 8:** Voltage Range 5.0 = 5.0V ±0.5V.

## Capacitance

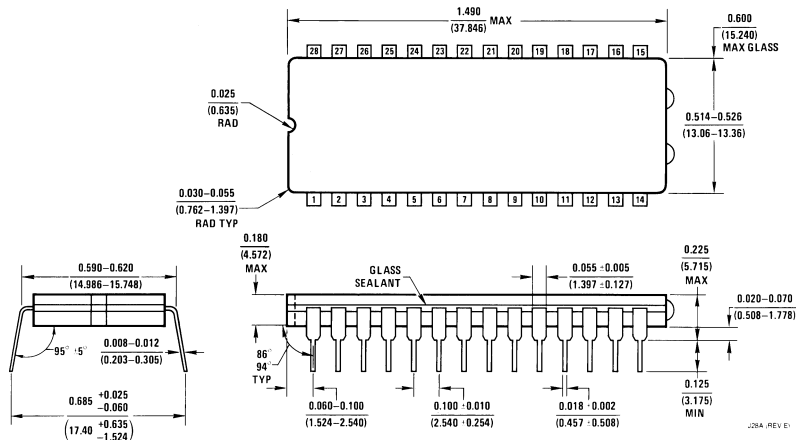
Symbol	Parameter	Typ	Units	Conditions
C <sub>IN</sub>	Input Capacitance	4.5	pF	V <sub>CC</sub> = 5.0V
C <sub>PD</sub>	Power Dissipation Capacitance	210	pF	V <sub>CC</sub> = 5.0V



**Physical Dimensions** inches (millimeters) unless otherwise noted



**28-Lead Plastic Chip Carrier (Q)**  
**NS Package Number E28A**




**28-Lead Plastic Chip Carrier (Q)**  
**NS Package Number J28A**

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